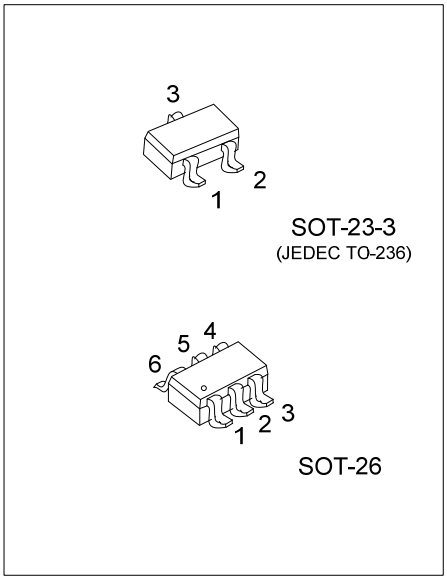
-2.0A, -20V P-CHANNEL POWER MOSFET



■ DESCRIPTION

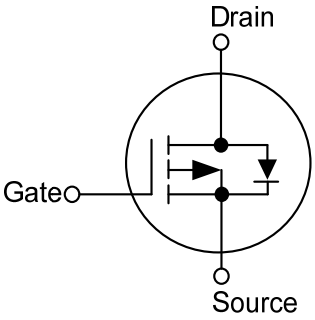
The UTC **UT2P02** is a P-channel MOSFET, it uses UTC's advanced technology to provide the customers with a minimum on state resistance and low gate charge, etc.

The UTC **UT2P02** is suitable for load switch and battery protection applications.

■ FEATURES

* $R_{DS(ON)}$ ≤ 170 mΩ @ V_{GS}=-4.5V, I_D=-1.0A
  $R_{DS(ON)}$ ≤ 300 mΩ @ V_{GS}=-2.5V, I_D=-0.5A
* Improved dv/dt capability
* Fast switching

■ SYMBOL



■ ORDERING INFORMATION

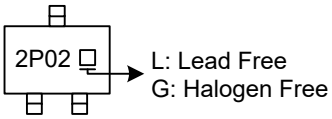
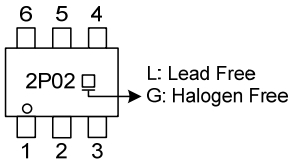
Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5	6	
UT2P02L-AE2-R	UT2P02G-AE2-R	SOT-23-3	G	S	D	-	-	-	Tape Reel
UT2P02L-AG6-R	UT2P02G-AG6-R	SOT-26	D	D	G	S	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UT2P02G-AE2-R

(1)Packing Type	(1) R: Tape Reel
(2)Package Type	(2) AE2: SOT-23-3, AG6: SOT-26
(3)Green Package	(3) G: Halogen Free and Lead Free, K: Lead Free

■ MARKING

SOT-23-3	SOT-26
	

■ ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current	Continuous	I_D	-2	A
	Pulsed (Note 2)	I_{DM}	-8	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	2	mJ
Power Dissipation	SOT-23-3	P_D	0.4	W
	SOT-26		0.5	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 0.1mH, I_{AS} = -6.35A, V_{DD} = -15V, R_G = 25Ω, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient (Note 3)	SOT-23-3	θ_{JA}	312	°C/W
	SOT-26		250	°C/W

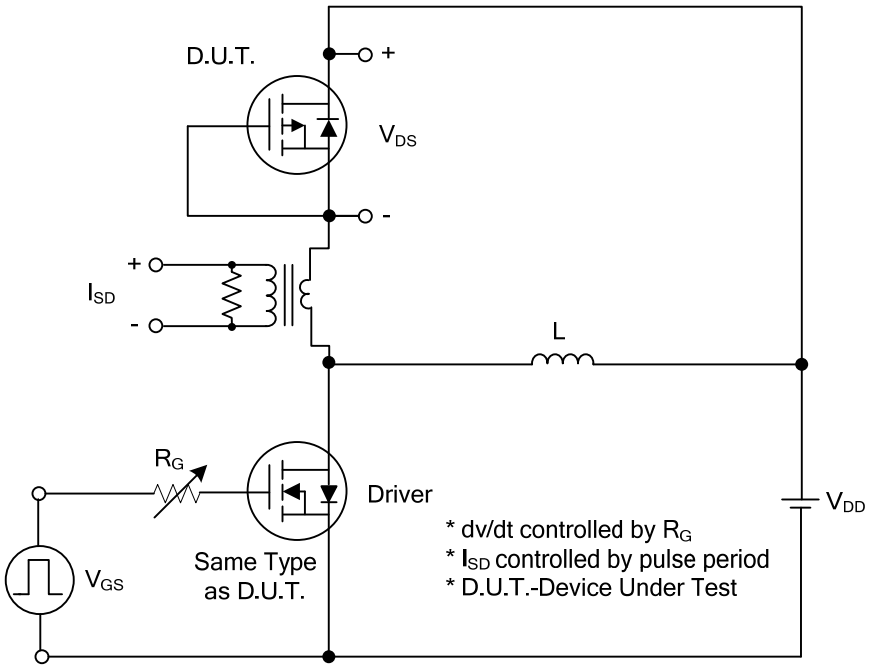
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

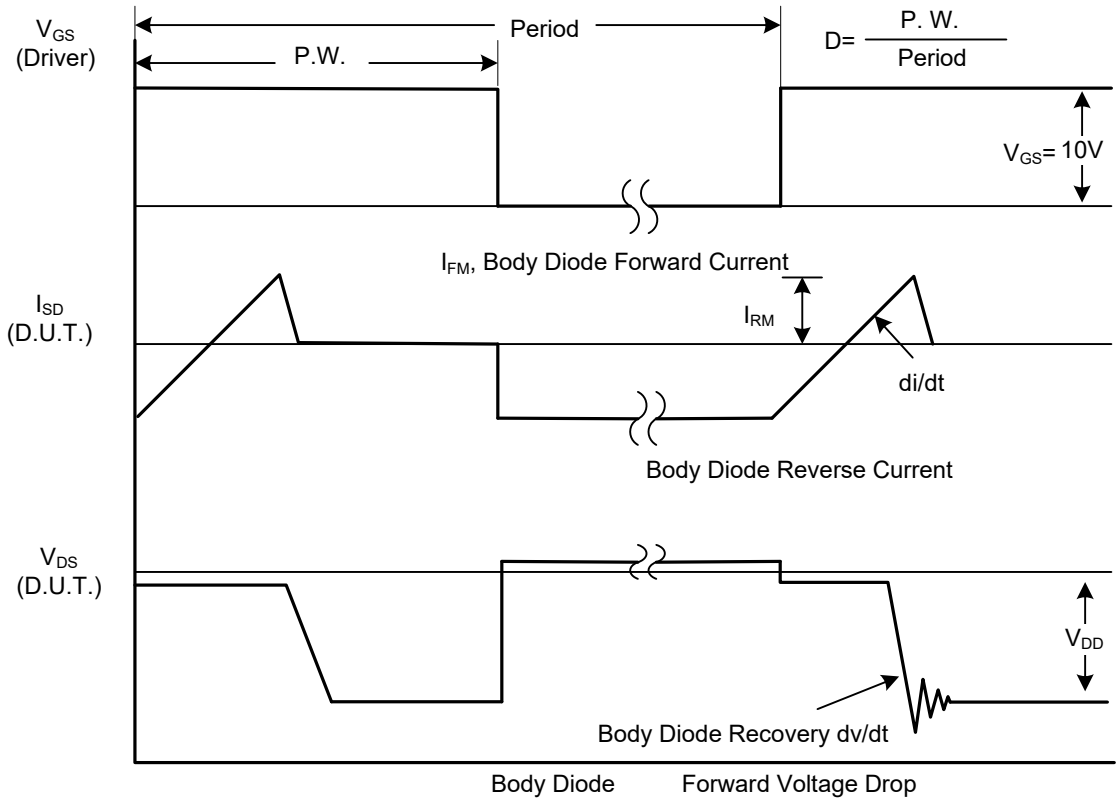
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=-250μA, V_{GS}=0V	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V, V_{GS}=0V			-1	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±12V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=-250μA	-0.5		-1.25	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-1.0A			170	mΩ
		V_{GS}=-2.5V, I_D=-0.5A			300	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=-5V, f=1.0MHz		250		pF
Output Capacitance	C_{OSS}			78		pF
Reverse Transfer Capacitance	C_{RSS}			60		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	V_{DS}=-16V, V_{GS}=-4.5V, I_D=-2.0A (Note 1, 2)		5.1		nC
Gate to Source Charge	Q_{GS}			1.2		nC
Gate to Drain Charge	Q_{GD}			1.26		nC
Turn-ON Delay Time	$t_{D(ON)}$	V_{DS}=-10V, V_{GS}=-4.5V, I_D=-2.0A, R_G=6Ω (Note 1, 2)		3.6		ns
Turn-ON Rise Time	t_R			18		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			44		ns
Turn-OFF Fall-Time	t_F			35		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				-2	A
Maximum Body-Diode Pulsed Current	I_{SM}				-8	A
Diode Forward Voltage	V_{SD}	I_S=-2.0A,V_{GS}=0V			-1.2	V

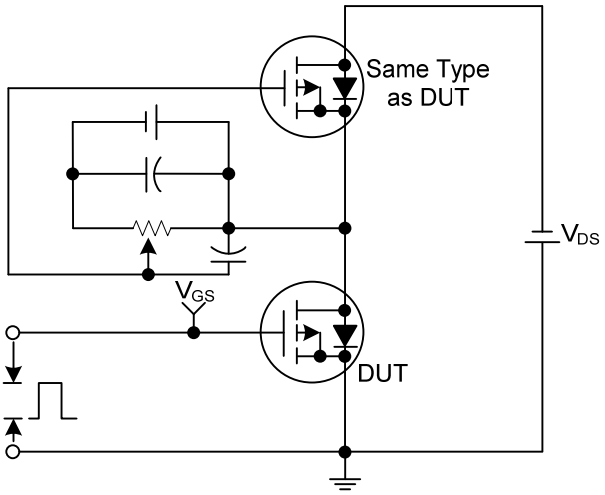
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

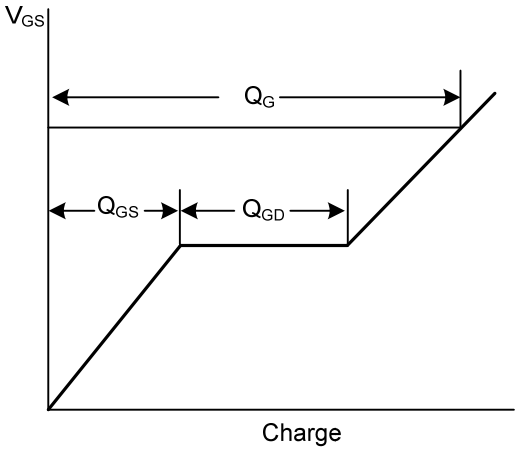




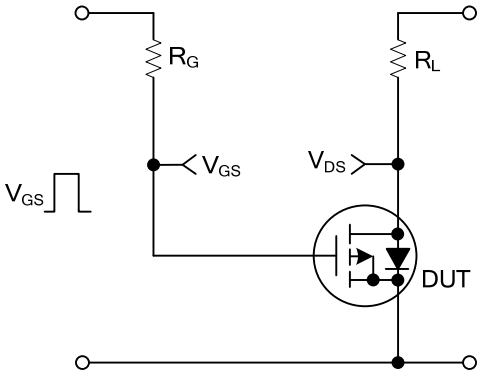
■ TEST CIRCUITS AND WAVEFORMS



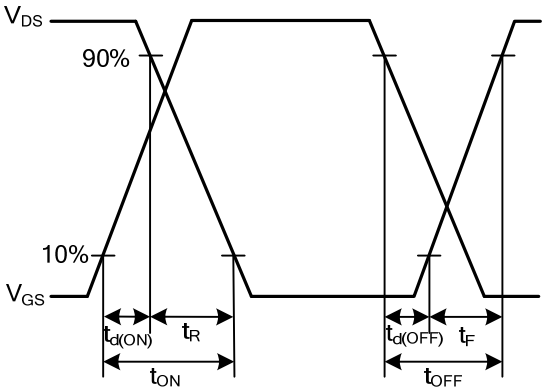
Gate Charge Test Circuit



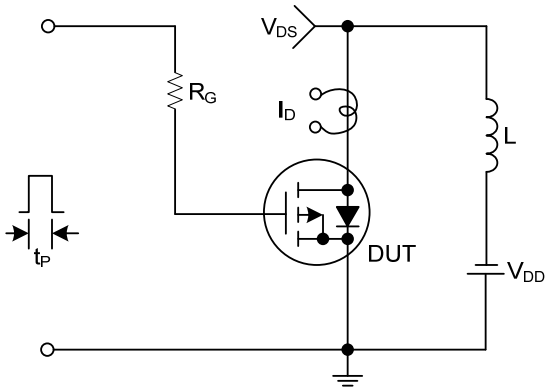
Gate Charge Waveforms



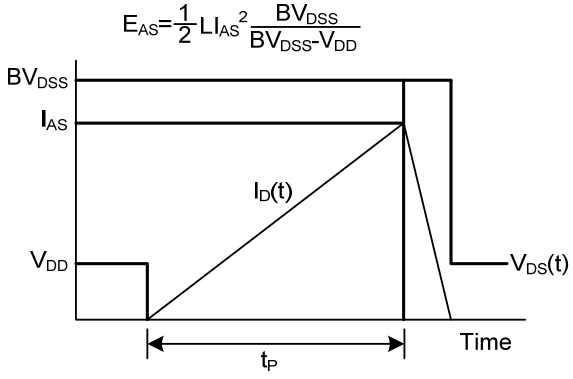
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms